

負の超磁歪を有する垂直磁化アモルファス SmFe_2 薄膜Amorphous SmFe_2 thin films with giant negative magnetostriction and perpendicular magnetic anisotropy

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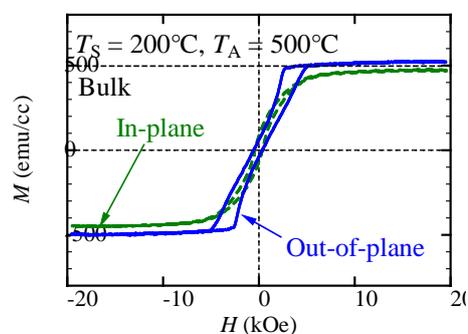
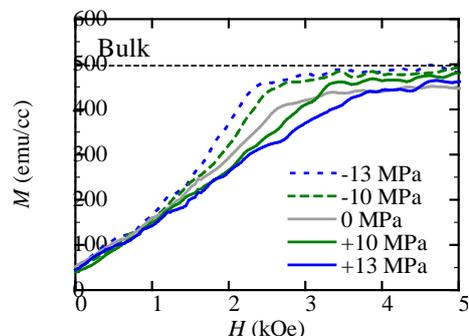
Strain-assisted magnetization reversal (SAMR) using inverse magnetostriction (IMS) magnetic tunnel junctions (MTJs) has possibility to reduce energy consumption during the magnetization switching [1]. The magnetostrictive free layer of our proposed IMS-MTJs needs to have perpendicular magnetic anisotropy (PMA) and large, negative magnetostrictive constant λ . SmFe_2 is promising as such a material since SmFe_2 is well-known materials with large, negative magnetostriction constant λ . In addition, some amorphous rare earth transition metal (RE-TM) alloys have been reported to show PMA [2]. In this paper, we systematically investigated magnetic anisotropy and magnetostriction of sputtered SmFe_2 films.

All the films were prepared with a facing targets sputtering system. The stack structure was quartz-substrate/W (20 nm)/ $\text{Sm}_{1.05}\text{Fe}_2$ (100 nm)/W (10 nm). The substrate temperature T_S during sputtering varied from RT to 400°C and post annealing temperature T_A also varied from 300°C to 600°C. X-ray diffraction analysis showed that all of $\text{Sm}_{1.05}\text{Fe}_2$ films had amorphous structure.

Figure 1 shows M - H curves for a typical $\text{Sm}_{1.05}\text{Fe}_2$ thin film exhibiting PMA. The difference between perpendicular and in-plane magnetic anisotropy energy density, ΔK , of the sample was determined to be 0.17 Merg/cc. We have found that $\text{Sm}_{1.05}\text{Fe}_2$ thin films formed at T_S below 200°C and annealed at T_A above 500°C showed clear PMA as indicated in Fig.1.

Demagnetization curves in the first quadrant under various applied pressures was shown in Fig. 2. The sample exhibited the inverse magnetostrictive effect with negative λ as magnetization energy reduced by compressive stress and increased by tensile stress. λ was estimated to be -920 ppm.

From these results, amorphous $\text{Sm}_{1.05}\text{Fe}_2$ thin films exhibited both of large, negative λ and PMA, and are promising as the free layer of IMS-MTJs for ultra-low power STT-MRAM.

[1] Y. Takamura, *et al.*, *Sol. St. Elec.*, **128**, 376 (2017).[2] V. G. Harris, *et al.*, *Phys. Rev. Lett.*, **69**, 1939 (1992).Fig. 1. M - H loops of a $\text{Sm}_{1.05}\text{Fe}_2$ thin film with $T_S = 200^\circ\text{C}$ and $T_A = 500^\circ\text{C}$ Fig. 2. Demagnetization curves with various applied pressures for the $\text{Sm}_{1.05}\text{Fe}_2$ thin film with $T_S = 200^\circ\text{C}$ and $T_A = 500^\circ\text{C}$